

MOSFET – N-Channel, POWERTRENCH®

100 V, 300 A, 2.0 mΩ



FDBL0200N100

Features

- Typical $R_{DS(on)} = 1.5 \text{ m}\Omega$ at $V_{GS} = 10 \text{ V}$, $I_D = 80 \text{ A}$
- Typical $Q_{g(\text{tot})} = 95 \text{ nC}$ at $V_{GS} = 10 \text{ V}$, $I_D = 80 \text{ A}$
- UIS Capability
- This Device is Pb-Free and is RoHS Compliant

Applications

- Industrial Motor Drive
- Industrial Power Supply
- Industrial Automation
- Battery Operated Tools
- Battery Protection
- Solar Inverters
- UPS and Energy Inverters
- Energy Storage
- Load Switch

ON Semiconductor®

www.onsemi.com

V_{DSS}	$R_{DS(ON) \text{ MAX}}$	$I_D \text{ MAX}$
100 V	2.0 mΩ @ 10 V	300 A



H-PSOF8L 11.68x9.80
CASE 100CU

MARKING DIAGRAM



\$Y = ON Semiconductor Logo
&Z = Assembly Plant Code
&3 = 3-Digit Plant Code
&K = 2-Digits Lot Run Traceability Code
FDBL0200N100 = Specific Device Code

ORDERING INFORMATION

See detailed ordering and shipping information on page 7 of this data sheet.

FDBL0200N100

MOSFET MAXIMUM RATINGS (T_J = 25°C unless otherwise noted)

Symbol	Rating	Value	Unit
V _{DSS}	Drain-to-Source Voltage	100	V
V _{GS}	Gate-to-Source Voltage	±20	V
I _D	Drain Current – Continuous (V _{GS} = 10) (Note 1)	T _C = 25°C	300
	Pulsed Drain Current	T _C = 25°C	See Figure 4
E _{AS}	Single Pulse Avalanche Energy (Note 2)	352	mJ
P _D	Power Dissipation	429	W
	Derate Above 25°C	2.9	W/°C
T _J , T _{STG}	Operating and Storage Temperature	-55 to +175	°C
R _{θJC}	Thermal Resistance, Junction to Case (Note 3)	0.35	°C/W
R _{θJA}	Thermal Resistance, Junction to Ambient (Note 3a)	43	°C/W
	Thermal Resistance, Junction to Ambient (Note 3b)	62.5	°C/W

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Current is limited by silicon.
2. Starting T_J = 25°C, L = 0.1 mH, I_{AS} = 84 A, V_{DD} = 100 V during inductor charging and V_{DD} = 0 V during time in avalanche.
3. R_{θJA} is the sum of the junction-to-case and case-to-ambient thermal resistance, where the case thermal reference is defined as the solder mounting surface of the drain pins. R_{θJC} is guaranteed by design, while R_{θJA} is determined by the board design.
 - a. 43°C/W when mounted on a 1 in² pad of 2 oz copper
 - b. 62.5°C/W when mounted on a minimum pad of 2 oz copper

FDBL0200N100

ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise noted)

Symbol	Parameter	Test Condition	Min	Typ	Max	Unit
--------	-----------	----------------	-----	-----	-----	------

OFF CHARACTERISTICS

B _{VDSS}	Drain-to-Source Breakdown Voltage	I _D = 250 μA, V _{GS} = 0 V	100	–	–	V
I _{DSS}	Drain-to-Source Leakage Current	V _{DS} = 100 V, V _{GS} = 0 V	T _J = 25°C	–	–	5 μA
			T _J = 175°C (Note 4)	–	–	2 mA
I _{GSS}	Gate-to-Source Leakage Current	V _{GS} = ±20V		–	–	±100 nA

ON CHARACTERISTICS

V _{GS(th)}	Gate to Source Threshold Voltage	V _{GS} = V _{DS} , I _D = 250 μA	2.0	3.1	4.5	V
R _{DS(on)}	Drain to Source On Resistance	I _D = 80 A, V _{GS} = 10 V	T _J = 25°C	–	1.5	2.0 mΩ
			T _J = 175°C (Note 4)	–	3.3	4.3 mΩ

DYNAMIC CHARACTERISTICS

C _{iss}	Input Capacitance	V _{DS} = 50 V, V _{GS} = 0 V, f = 1 MHz	–	6970	9760	pF
C _{oss}	Output Capacitance		–	3950	5530	pF
C _{rss}	Reverse Transfer Capacitance		–	29	41	pF
R _g	Gate Resistance	f = 1 MHz	–	0.45	1	Ω
Q _{g(ToT)}	Total Gate Charge at 10 V	V _{GS} = 0 to 10 V, V _{DD} = 80 V, I _D = 80 A	–	95	133	nC
Q _{g(th)}	Threshold Gate Charge	V _{GS} = 0 to 2 V, V _{DD} = 80 V, I _D = 80 A	–	13	–	nC
Q _{gs}	Gate-to-Source Gate Charge	V _{DD} = 80 V, I _D = 80 A	–	31	–	nC
Q _{gd}	Gate-to-Drain "Miller" Charge		–	20	–	nC

SWITCHING CHARACTERISTICS

t _{on}	Turn-On Time	V _{DD} = 50 V, I _D = 80 A, V _{GS} = 10 V, R _{GEN} = 6 Ω	–	–	73	ns
t _{d(on)}	Turn-On Delay		–	31	50	ns
t _r	Rise Time		–	25	40	ns
t _{d(off)}	Turn-Off Delay		–	36	58	ns
t _f	Fall Time		–	9	18	ns
t _{off}	Turn-Off Time		–	–	59	ns

DRAIN-SOURCE DIODE CHARACTERISTICS

V _{SD}	Source-to-Drain Diode Voltage	I _{SD} = 80 A, V _{GS} = 0 V	–	–	1.25	V
		I _{SD} = 40 A, V _{GS} = 0 V	–	–	1.2	V
t _{rr}	Reverse-Recovery Time	I _F = 80 A, dI _{SD} /dt = 100 A/μs, V _{DD} = 80 V	–	115	184	ns
			–	172	273	nC

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

TYPICAL CHARACTERISTICS

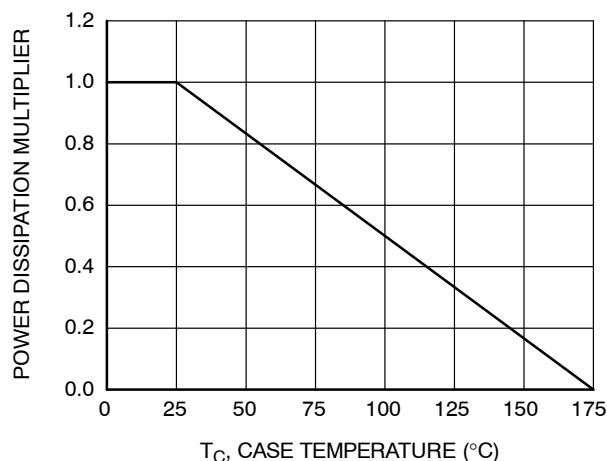


Figure 1. Normalized Power Dissipation vs. Case Temperature

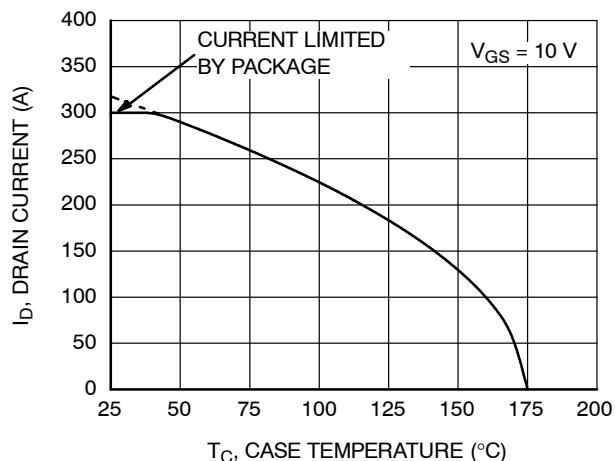


Figure 2. Maximum Drain Current vs. Case Temperature

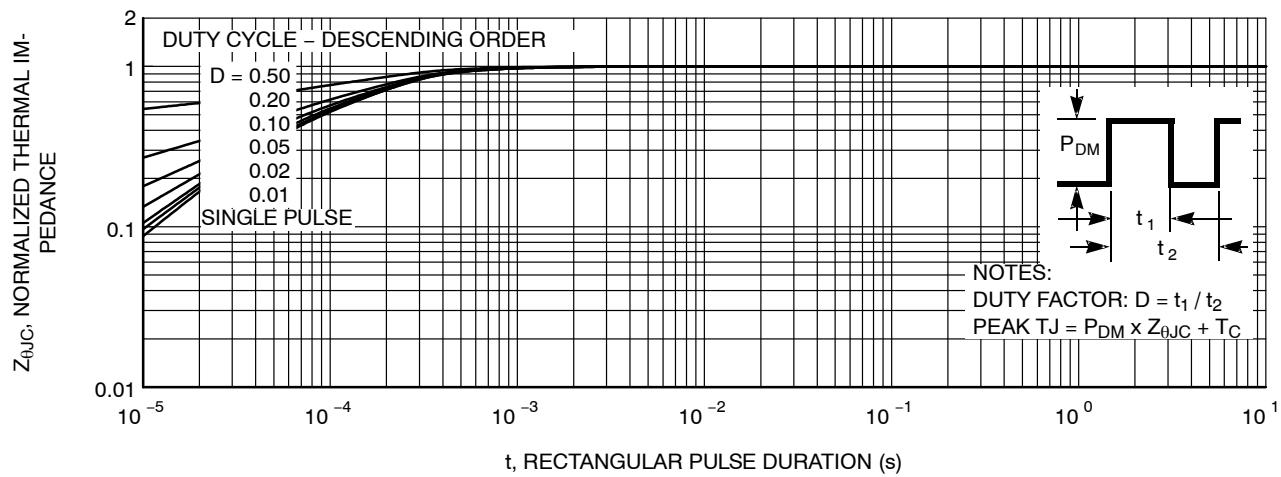


Figure 3. Normalized Maximum Transient Thermal Impedance

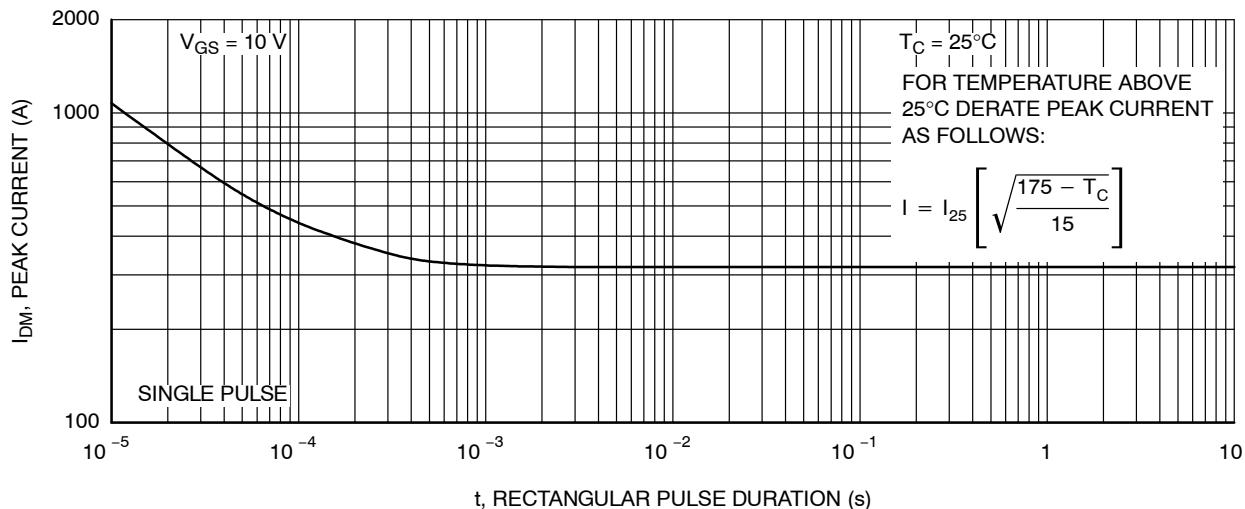
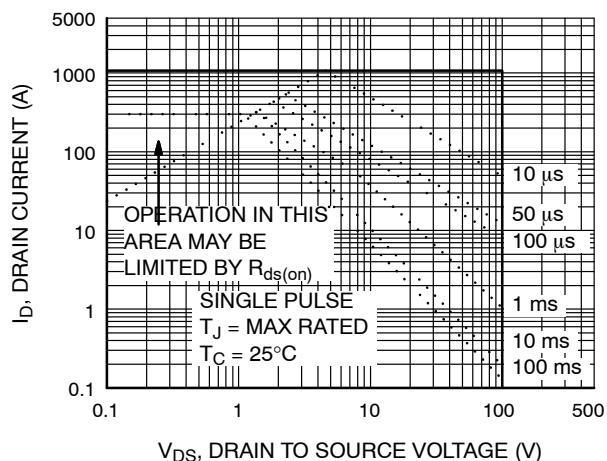
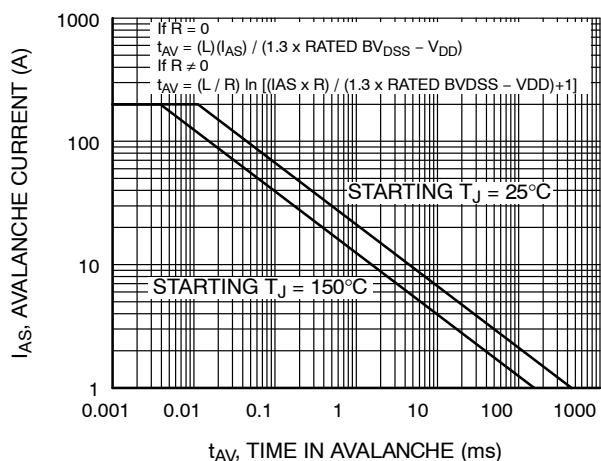
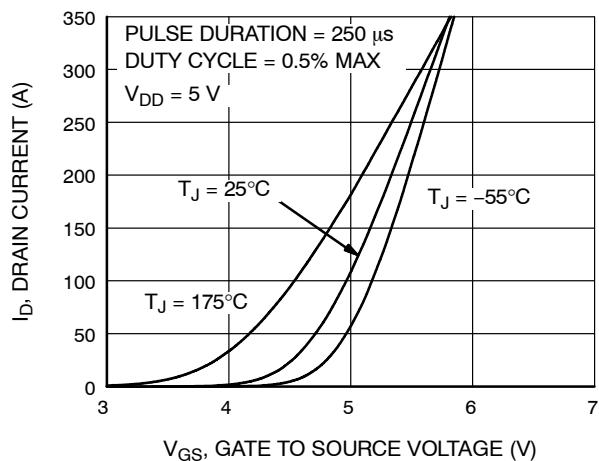
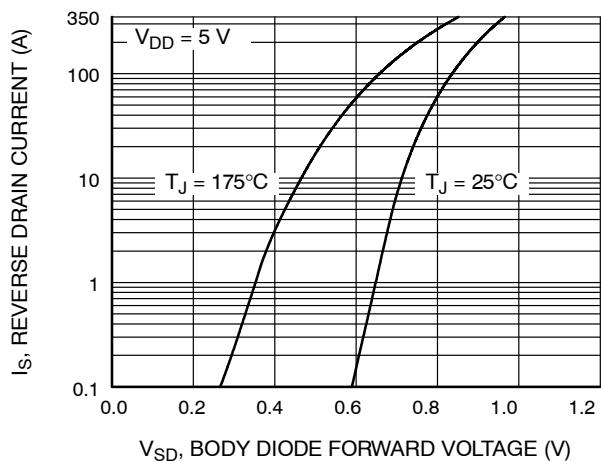
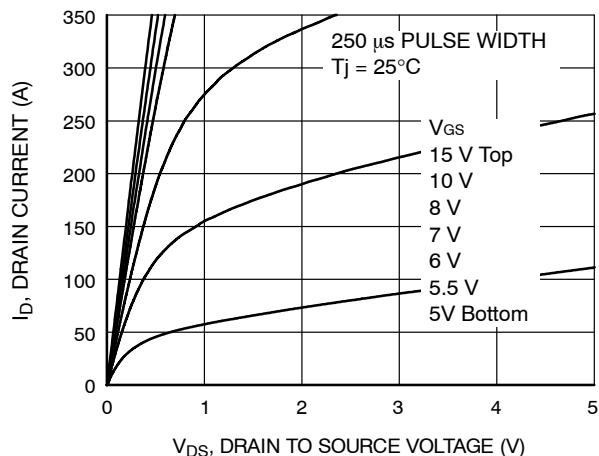
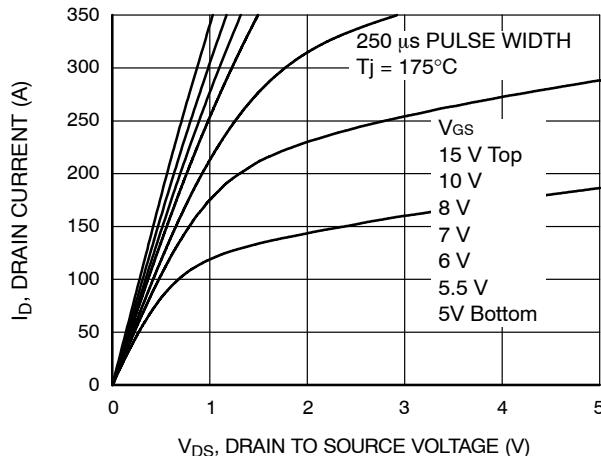
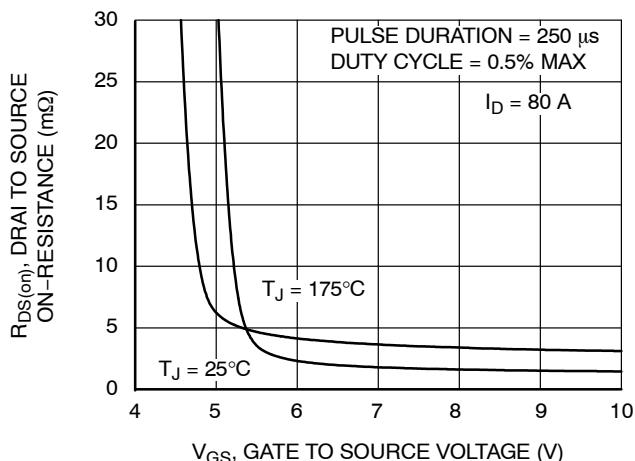
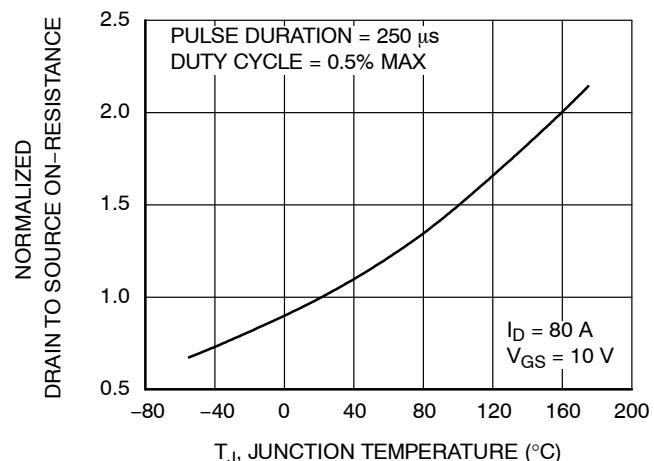
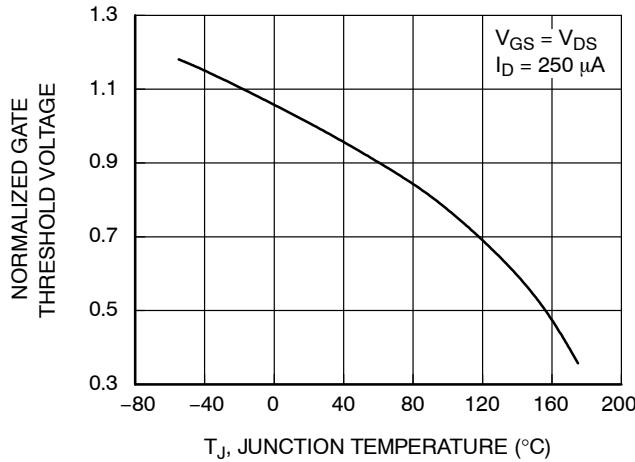
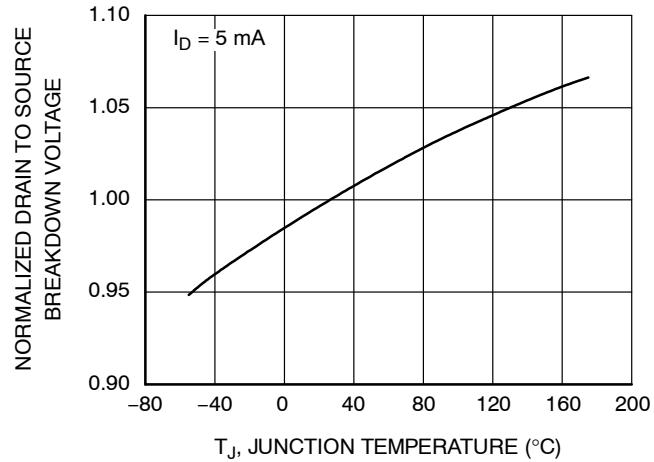
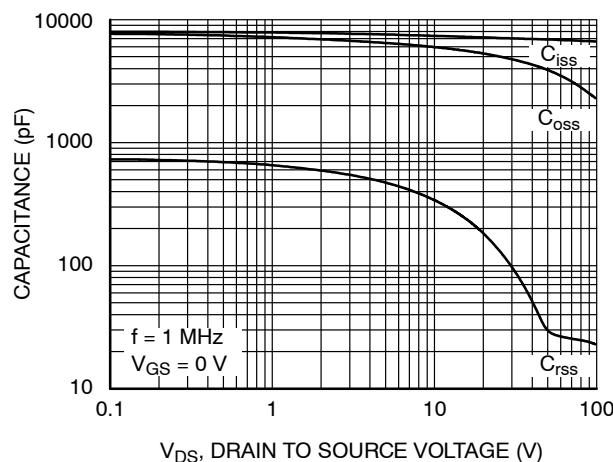
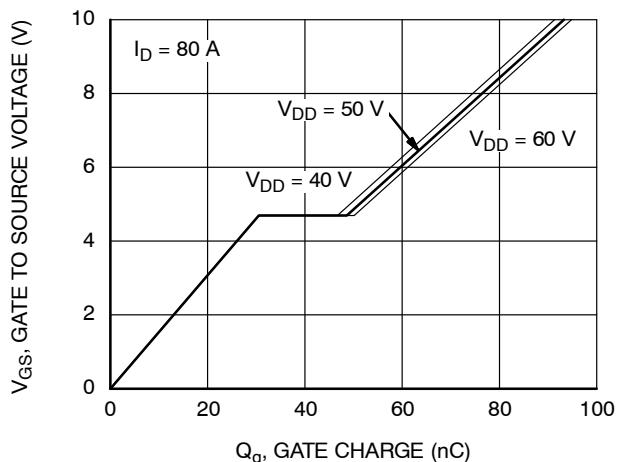


Figure 4. Peak Current Capability

TYPICAL CHARACTERISTICS (continued)

Figure 5. Forward Bias Safe Operating Area


NOTE: Refer to ON Semiconductor Application Notes [AN-7514](#) and [AN-7515](#)

Figure 6. Unclamped Inductive Switching Capability

Figure 7. Transfer Characteristics

Figure 8. Forward Diode Characteristics

Figure 9. Saturation Characteristics

Figure 10. Saturation Characteristics

TYPICAL CHARACTERISTICS (continued)

Figure 11. $R_{DS(on)}$ vs. Gate Voltage

Figure 12. Normalized $R_{DS(on)}$ vs. Junction Temperature

Figure 13. Normalized Gate Threshold Voltage vs. Temperature

Figure 14. Normalized Drain to Source Breakdown Voltage vs. Junction Temperature

Figure 15. Capacitance vs. Drain to Source Voltage

Figure 16. Gate Charge vs. Gate to Source Voltage

FDBL0200N100

ORDERING INFORMATION

Device	Device Marking	Package Type	Reel Size	Tape Width	Shipping [†]
FDBL0200N100	FDBL0200N100	H-PSOF8L 11.68x9.80 (Pb-Free)	13"	24 mm	2000 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

POWERTRENCH is registered trademark of Semiconductor Components Industries, LLC (SCILLC) or its subsidiaries in the United States and/or other countries.

MECHANICAL CASE OUTLINE

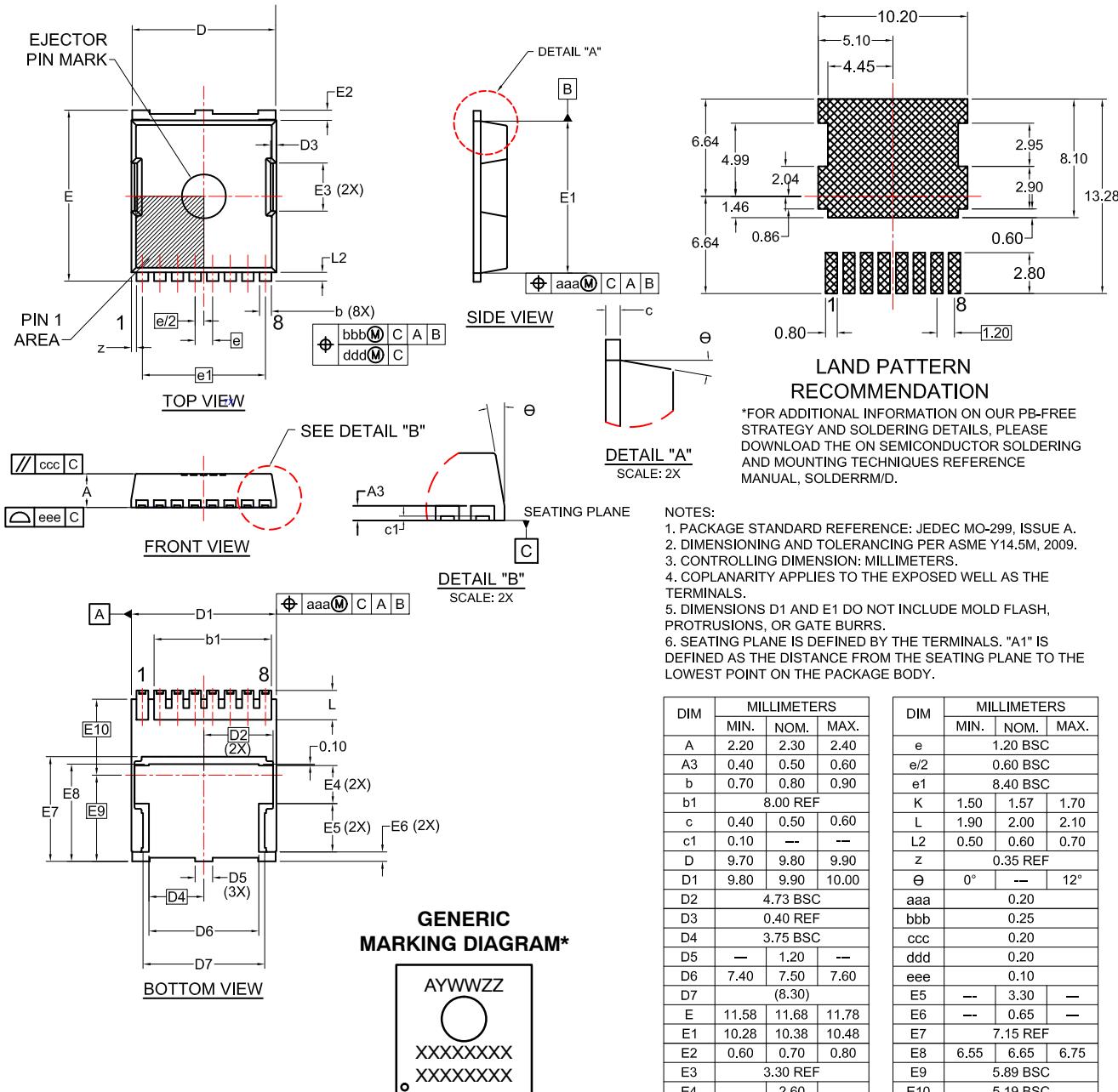
PACKAGE DIMENSIONS

ON Semiconductor®



H-PSOF8L 11.68x9.80
CASE 100CU
ISSUE A

DATE 06 JAN 2020



*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "■", may or may not be present. Some products may not follow the Generic Marking.

DOCUMENT NUMBER:	98AON13813G	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.
DESCRIPTION:	H-PSOF8L 11.68x9.80	PAGE 1 OF 1

ON Semiconductor and **ON** are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. ON Semiconductor does not convey any license under its patent rights nor the rights of others.

onsemi, ONSEMI, and other names, marks, and brands are registered and/or common law trademarks of Semiconductor Components Industries, LLC dba "**onsemi**" or its affiliates and/or subsidiaries in the United States and/or other countries. **onsemi** owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of **onsemi**'s product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. **onsemi** reserves the right to make changes at any time to any products or information herein, without notice. The information herein is provided "as-is" and **onsemi** makes no warranty, representation or guarantee regarding the accuracy of the information, product features, availability, functionality, or suitability of its products for any particular purpose, nor does **onsemi** assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using **onsemi** products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by **onsemi**. "Typical" parameters which may be provided in **onsemi** data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. **onsemi** does not convey any license under any of its intellectual property rights nor the rights of others. **onsemi** products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use **onsemi** products for any such unintended or unauthorized application, Buyer shall indemnify and hold **onsemi** and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that **onsemi** was negligent regarding the design or manufacture of the part. **onsemi** is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:

Email Requests to: orderlit@onsemi.com

onsemi Website: www.onsemi.com

TECHNICAL SUPPORT

North American Technical Support:

Voice Mail: 1 800-282-9855 Toll Free USA/Canada
Phone: 011 421 33 790 2910

Europe, Middle East and Africa Technical Support:

Phone: 00421 33 790 2910

For additional information, please contact your local Sales Representative